

IN THE CLAIMS

Please amend claim 31.

Please add new claims 55 - 62.

Please enter the pending claims as follows:

1. - 30. (Canceled)

31. (Currently Amended) A method comprising:

providing a substrate;

forming a metal layer over said substrate, said metal layer comprising a bond pad and a first member, said bond pad and said first member being separated by a gap;

forming a first material over said bond pad and over said first member, said first material having a low dielectric constant, said first material having ~~at least a minimum thickness that is sufficient to completely fill said gap, said first material doped with fluorine atoms;~~

forming a second material over said first material, said second material being thin and resistant to moisture penetration, said second material being kept above said bond pad and said first member and out of said gap;

forming a third material over said second material;

forming an opening with tapered sidewalls through in said third material ~~[[,]]~~ and vertical sidewalls in said second material ~~[[,]]~~ and said first material to expose a top surface of said bond pad, ~~said opening having sidewalls comprising edges of said second material and said first material;~~

forming a fourth material barrier layer over said ~~third second~~ material, said tapered and vertical sidewalls of said opening, and said top surface of said bond pad, said fourth material barrier layer being conductive, said fourth material barrier layer having a thickness ~~sufficient~~ to prevent moisture penetration; and

forming a bump on said fourth material over said sidewalls of said opening and over said top surface of said bond pad.

32. (Previously Presented) The method of claim 31 wherein said gap has a high aspect ratio.

33. (Previously Presented) The method of claim 32 wherein said high aspect ratio is around 2.0.

34. (Previously Presented) The method of claim 31 wherein said first material has a dielectric constant of less than 4.0.

35. (Previously Presented) The method of claim 31 wherein said first material is silicon dioxide.

36. (Previously Presented) The method of claim 31 wherein said first material is doped with fluorine atoms to reduce dielectric constant.

37. (Previously Presented) The method of claim 31 wherein said second material is hermetic.

38. (Previously Presented) The method of claim 31 wherein said second material is silicon nitride.

39. (Previously Presented) The method of claim 38 wherein said silicon nitride has a thickness of between 500 – 1,500 Angstroms.

40. - 54. (Canceled)

55. (New) The method of claim 31 wherein said third material comprises photodefinable polyimide.

56. (New) The method of claim 31 wherein said third material has a thickness of between 2.0 – 10.0 microns.

57. (New) The method of claim 31 wherein said third material comprises CVD deposited silicon dioxide.

58. (New) The method of claim 31 wherein said third material provides stress relief.

59. (New) The method of claim 31 wherein said third material provides scratch protection for said second material.

60. (New) The method of claim 31 wherein said fourth material comprises a barrier layer.

61. (New) The method of claim 31 wherein said fourth material comprises a dual layer film.

62. (New) The method of claim 31 wherein said fourth material comprises a lower titanium film and an upper nickel vanadium film.